

Supplemental material

Localization effect in photoelectron transport induced by alloy disorder in nitride semiconductor compounds

Mylène Sauty¹, Nicolas M. S. Lopes¹, Jean-Philippe Banon¹, Yves Lassailly¹, Lucio Martinelli¹, Abdullah Alhassan², Yi Chao Chow², Shuji Nakamura², James S. Speck², Claude Weisbuch^{1,2}, Jacques Peretti¹

¹Laboratoire de Physique de la Matière Condensée, Ecole polytechnique,
CNRS, Institut Polytechnique de Paris, 91120 Palaiseau, France

²Materials Department, University of California, Santa Barbara, California 93106, USA

The low energy photoemission quantum yield excitation spectra, recorded at different temperatures between 140K and 300K, for the InGaN samples with 2% and 5% indium content, are plotted here below.

